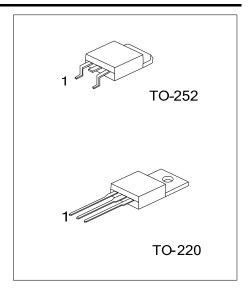
UTT20N10 Power MOSFET

20A, 100V N-CHANNEL **POWER MOSFET**

DESCRIPTION

The UTC UTT20N10 is a N-channel enhancement mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

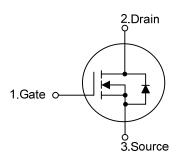
The UTC UTT20N10 is universally applied in low voltage, such as automotive, high efficiency switching for DC/DC converters, and DC motor control.



FEATURES

- * $R_{DS(on)}$ < 0.12 Ω @ V_{GS} = 10 V
- * Typically 32pF low C_{RSS}
- * High switching speed
- * Typically 19nC low gate charge

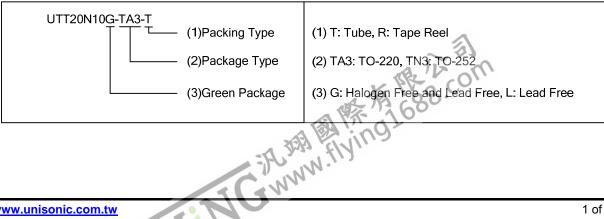
SYMBOL



ORDERING INFORMATION

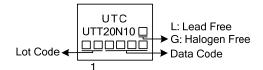
Ordering Number		Dookogo	Pin Assignment			Dealing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTT20N10L-TA3-T	UTT20N10G-TA3-T	TO-220	G	D	S	Tube	
UTT20N10L-TN3-R	UTT20N10G-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate S: Source D: Drain



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MARKING





UTT20N10 Power MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	100	V	
Gate-Source Voltage		V_{GSS}	±25	V	
Drain Current	Continuous	I _D	20	Α	
	Pulsed	I _{DM}	80	Α	
Power Dissipation	TO-220	Ь	62.5	W	
	TO-252	P _D	50		
Junction Temperature		TJ	+150	°C	
Storage Temperature	_	T _{STG}	-40 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER .		SYMBOL	RATINGS	UNIT	
Junction to Ambient	TO-220	0	62.5	°C/W	
	TO-252	θ _{JA}	100		
Junction to Case	TO-220	θЈС	2	°C/W	
	TO-252		2.5	C/VV	

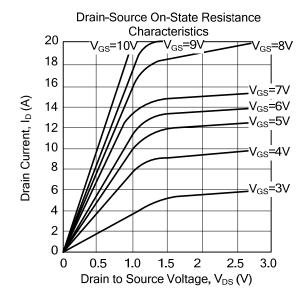
ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

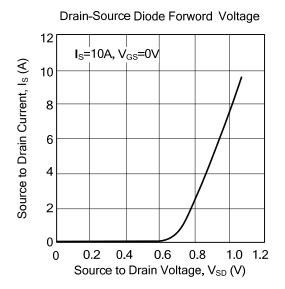
PARAMETER		SYMBOL	L TEST CONDITIONS		TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	100			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μΑ
Gate- Source Leakage Current	Forward		V_{GS} =+25V, V_{DS} =0V			+100	nA
	Reverse	I _{GSS}	V _{GS} =-25V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0		3.0	V
Static Drain-Source On-State Re	esistance	R _{DS(ON)}	V_{GS} =10V, I_D =20A			120	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}			600	780	pF
Output Capacitance		Coss	V_{GS} =0V, V_{DS} =25V, f=1.0MHz		165	215	pF
Reverse Transfer Capacitance		C_{RSS}			32	40	pF
SWITCHING PARAMETERS							
Total Gate Charge	otal Gate Charge		\/ =10\/ \/ =20\/ =10A		19	25	nC
Gate to Source Charge		Q_GS	V _{GS} =10V, V _{DS} =80V, I _D =19A (Note 1, 2)		3.9		nC
Gate to Drain Charge		Q_GD	(Note 1, 2)		9.0		nC
Turn-ON Delay Time		$t_{D(ON)}$			7.5	25	ns
Rise Time		t_R	V_{DD} =50V, I_{D} =1A, R_{L} =50 Ω ,		150	310	ns
Turn-OFF Delay Time		t _{D(OFF)}	V_{GS} =10V, R_{G} =25 Ω (Note 1, 2)		20	50	ns
Fall-Time		t_{F}			65	140	ns
SOURCE- DRAIN DIODE RATII	NGS AND	CHARACTERI	STICS				
Maximum Body-Diode Continuou	us Current	Is				20	Α
Maximum Body-Diode Pulsed Current		I _{SM}				80	Α
Drain-Source Diode Forward Vol	ltage	V_{SD}	I _S =20A, V _{GS} =0V			1.5	V
Notes: 1. Pulse Test: Pulse width 2. Essentially independer	n≤300µs, D nt of operati	uty cycle≤2%. ng temperature	I _S =20A, V _{GS} =0V				
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^{2.} Essentially independent of operating temperature.

■ TYPICAL CHARACTERISTICS





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